

Silicon PNP Power Transistors

2SB434

DESCRIPTION

- With TO-220 package
- Complement to type 2SD234

APPLICATIONS

- For low frequency power amplifier and switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

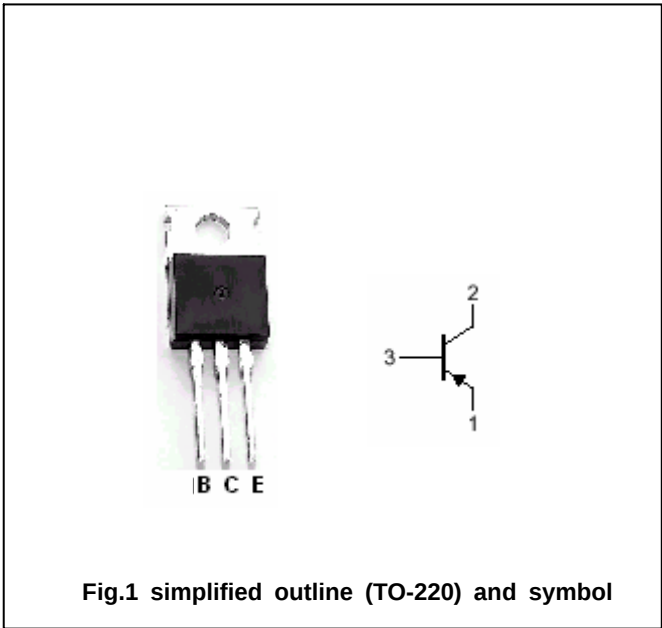


Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-60	V
V_{CEO}	Collector-emitter voltage	Open base	-50	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-3	A
P_C	Collector power dissipation		1.5	W
		$T_C=25$	25	
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-5mA, I _B =0	-50			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-1mA, I _E =0	-60			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1mA, I _C =0	-6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-3A; I _B =-0.3A			-1.2	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-3A; I _B =-0.3A			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-40V; I _E =0			-10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-4V; I _C =0			-10	μA
h _{FE}	DC current gain	I _C =-0.5A; V _{CE} =-1V	40		240	
C _{OB}	Output capacitance	I _E =0; V _{CB} =-10V, f=1MHz		90		pF
f _T	Transition frequency	I _C =-0.5A; V _{CE} =-10V		3		MHz

◆ h_{FE} Classifications

R	O	Y
40-80	70-140	120-240

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PACKAGE OUTLINE

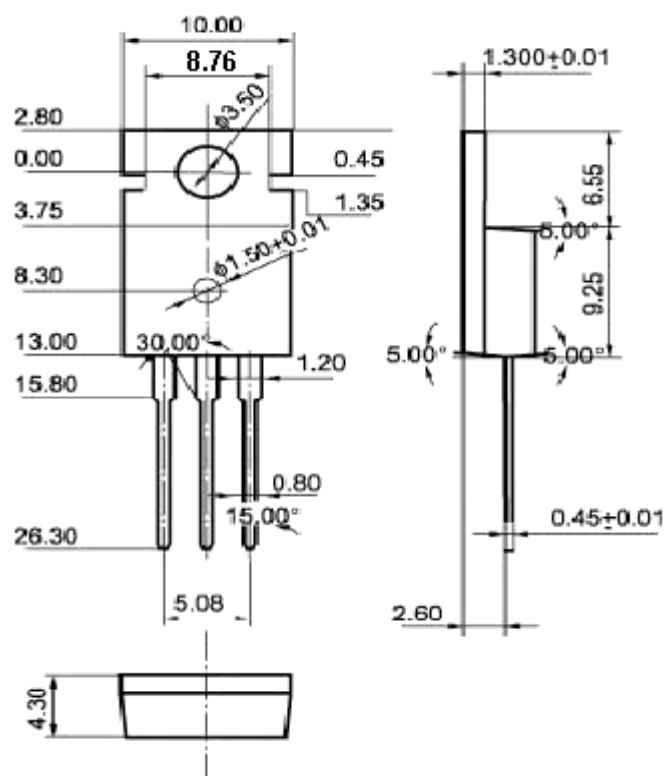


Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)